

Application No.: 09/849,530

Docket No.: FIS919980172US2  
20136-00344-US**AMENDMENTS TO THE CLAIMS**

Claim 15 is currently amended.

1-14 (canceled)

15. (currently amended) A process for fabricating a semiconductor structure which comprises providing a germanium-containing layer of at least one member selected from the group consisting of ~~copper germanide~~, germanium oxide, germanium nitride and combinations thereof onto at least one surface of a copper member; and providing a layer of a material that is poorly adherent to copper on the germanium-containing layer.

16. (original) The process of claim 15 which comprises providing a germanium-containing layer by selectively forming copper germanide on the copper member by flowing germane over the structure.

17. (original) The process of claim 16 wherein the germane is at a temperature of about 200 to about 450°C.

18. (original) The process of claim 16 which comprises providing a gaseous composition containing about 0.05 to about 5% of germane and a second gas selected from the group consisting of nitrogen, helium, argon, and mixtures thereof.

19. (original) The process of claim 15 wherein the germanium-containing layer is provided by providing a layer of copper germanide on the copper and then oxidizing all or a portion of the copper germanide to provide a layer of germanium oxide.

20. (original) The process of claim 15 wherein the thickness of the germanium-containing layer is about 100 to about 1000 Å.

21. (original) The process of claim 15 wherein the thickness of the germanium-containing layer is about 150 to about 400 Å.

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22. (original) The process of claim 19 wherein the layer of copper germanide is about 100 to about 1000 Å and the layer of germanium oxide is about 100 to about 1000 Å.

23. (original) The process of claim 15 wherein the germanium-containing layer comprises providing a layer of copper germanide and then nitriding all or a portion of the copper germanide layer to provide germanium nitride.

24. (original) The process of claim 23 wherein the copper germanide layer is about 100 to about 1000 Å thick and the germanium nitride layer is about 100 to about 1000 Å thick.

25. (original) The process of claim 15 wherein the germanium-containing layer is provided by providing a layer of copper germanide on the copper, then oxidizing all or a portion of the copper germanide to provide a layer of germanium oxide, and then nitriding a portion of the copper oxide layer to provide germanium nitride.

26. (original) The process of claim 15 wherein the copper member is copper or a copper alloy.

27. (original) The process of claim 15 wherein the copper member is about 1000 to about 20,000 Å thick.

28. (previously presented) The process of claim 29 wherein the layer of silicon nitride is about 100 to about 200000 Å thick.

29. (previously presented) The process of claim 15 wherein the material that is poorly adherent to copper is silicon nitride.

30. (previously presented) The process of claim 15 wherein the material that is poorly adherent to copper is silicon dioxide.

31. (canceled)